DG758BX45

Gate Turn-off Thyristor

Replaces March 1998 version, DS4095-5.3

DS4095-6.0 January 2000

APPLICATIONS

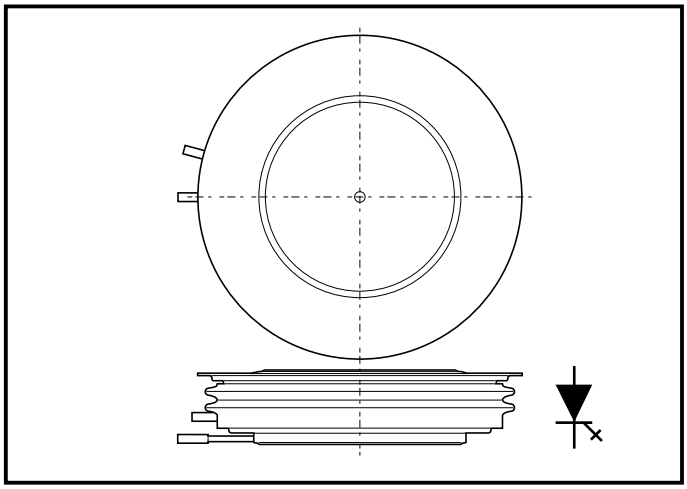
- Variable speed A.C. motor drive inverters (VSD-AC).
- Uninterruptable Power Supplies
- High Voltage Converters.
- Choppers.
- Welding.
- Induction Heating.
- DC/DC Converters.

KEY PARAMETERS

I_{TCM}	3000A
V_{DRM}	4500V
$I_{T(AV)}$	870A
dV_D/dt	1000V/µs
di_T/dt	300A/µs

FEATURES

- Double Side Cooling.
- High Reliability In Service.
- High Voltage Capability.
- Fault Protection Without Fuses.
- High Surge Current Capability.
- Turn-off Capability Allows Reduction In Equipment Size And Weight. Low Noise Emission Reduces Acoustic Cladding Necessary For Environmental Requirements.



Outline type code: X.
See Package Details for further information.

VOLTAGE RATINGS

Type Number	Repetitive Peak Off-state Voltage V_{DRM} V	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DG758BX45	4500	16	T_{vj} = 125°C, I_{DM} = 100mA, I_{RRM} = 50mA

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TCM}	Repetitive peak controllable on-state current	V_D = 66% V_{DRM}, T_j = 125°C, di_{GQ}/dt = 40A/µs, Cs = 6µF	3000	A
$I_{T(AV)}$	Mean on-state current	T_{HS} = 80°C. Double side cooled. Half sine 50Hz.	870	A
$I_{T(RMS)}$	RMS on-state current	T_{HS} = 80°C. Double side cooled. Half sine 50Hz.	1365	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine. T_j = 125°C	16.0	kA
I^2t	I^2t for fusing	10ms half sine. T_j =125°C	1.28×10^6	A^2s
di_T/dt	Critical rate of rise of on-state current	V_D = 3000V, I_T = 3000A, T_j = 125°C, I_{FG} > 40A, Rise time > 1.0µs	300	A/µs
dV_D/dt	Rate of rise of off-state voltage	To 66% V_{DRM}; $R_{GK} \leq 1.5\Omega$, T_j = 125°C	100	V/µs
		To 66% V_{DRM}; V_{RG} = -2V, T_j = 125°C	1000	V/µs
L_S	Peak stray inductance in snubber circuit	-	200	nH

GATE RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
V_{RGM}	Peak reverse gate voltage	This value maybe exceeded during turn-off	-	16	V
I_{FGM}	Peak forward gate current		-	100	A
$P_{FG(AV)}$	Average forward gate power		-	20	W
P_{RGM}	Peak reverse gate power		-	24	kW
di_{GQ}/dt	Rate of rise of reverse gate current		30	60	A/µs
$t_{ON(min)}$	Minimum permissable on time		50	-	µs
$t_{OFF(min)}$	Minimum permissable off time		100	-	µs

THERMAL RATINGS AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-hs)}$	DC thermal resistance - junction to heatsink surface	Double side cooled		-	0.0146	°C/W
		Anode side cooled		-	0.0233	°C/W
		Cathode side cooled		-	0.0392	°C/W
$R_{th(c-hs)}$	Contact thermal resistance	Clamping force 35.0kN With mounting compound	per contact	-	0.0036	°C/W
T_{vj}	Virtual junction temperature			-40	125	°C
T_{OP}/T_{stg}	Operating junction/storage temperature range			-40	125	°C
-	Clamping force			33.0	37.0	kN

CHARACTERISTICS

T_j = 125°C unless stated otherwise					
Symbol	**Parameter**	**Conditions**	**Min.**	**Max.**	**Units**
V_{TM}	On-state voltage	At 3000A peak, $I_{G(ON)}$ = 8A d.c.	-	4.0	V
I_{DM}	Peak off-state current	V_{DRM} = 4500V, V_{RG} = 0V	-	100	mA
I_{RRM}	Peak reverse current	At V_{RRM}	-	50	mA
V_{GT}	Gate trigger voltage	V_D = 24V, I_T = 100A, T_j = 25°C	-	1.2	V
I_{GT}	Gate trigger current	V_D = 24V, I_T = 100A, T_j = 25°C	-	3.5	A
I_{RGM}	Reverse gate cathode current	V_{RGM} = 16V, No gate/cathode resistor	-	50	mA
E_{ON}	Turn-on energy	V_D = 2250V	-	3000	mJ
t_d	Delay time	I_T = 3000A, dI_T/dt = 300A/µs	-	1.5	µs
t_r	Rise time	I_{FG} = 40A, rise time < 1.0µs	-	3.0	µs
E_{OFF}	Turn-off energy	I_T = 3000A, V_{DM} = 3000V Snubber Cap Cs = 6.0µF, di_{GQ}/dt = 40A/µs	-	6300	mJ
t_{gs}	Storage time		-	20.6	µs
t_{gf}	Fall time		-	2.2	µs
t_{gq}	Gate controlled turn-off time		-	22.8	µs
Q_{GQ}	Turn-off gate charge		-	10000	µC
Q_{GQT}	Total turn-off gate charge		-	20000	µC
I_{GQM}	Peak reverse gate current		-	830	A

CURVES

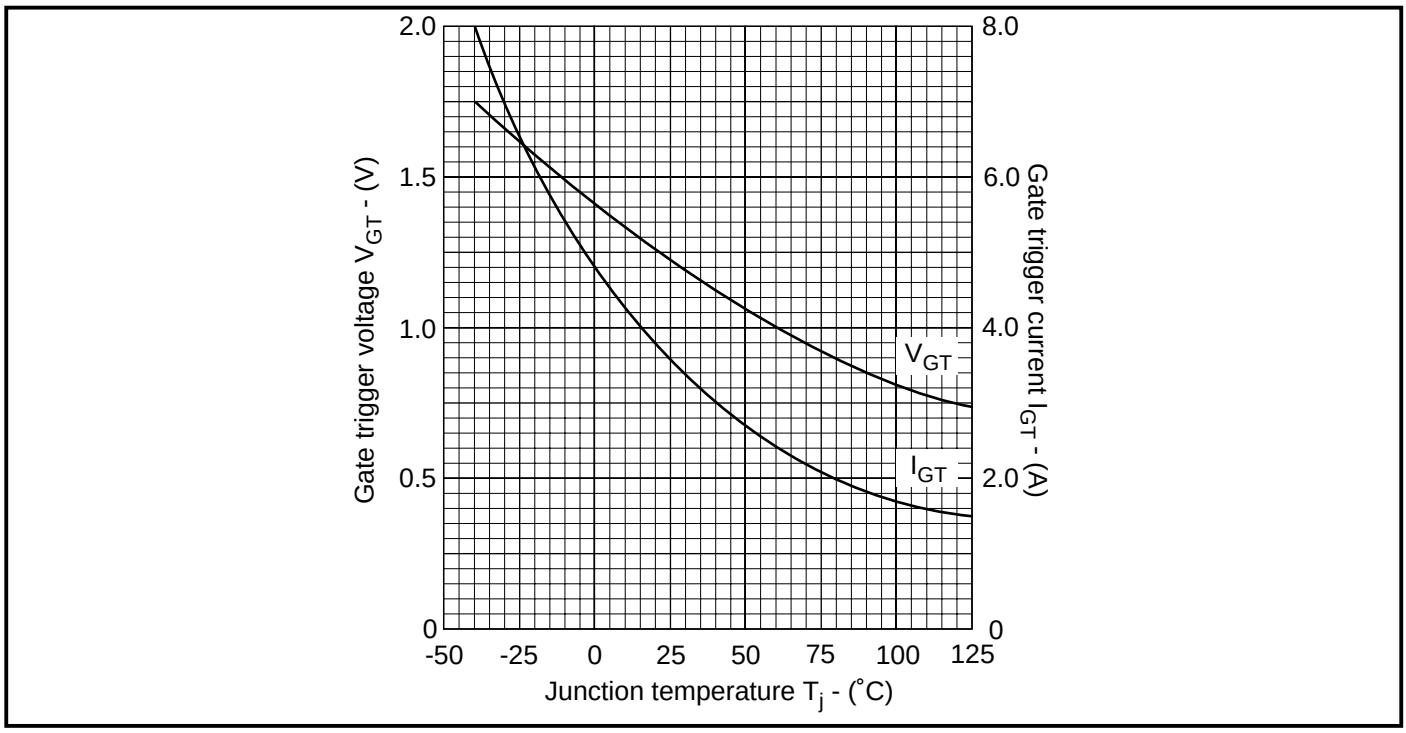


Fig.1 Maximum gate trigger voltage/current vs junction temperature

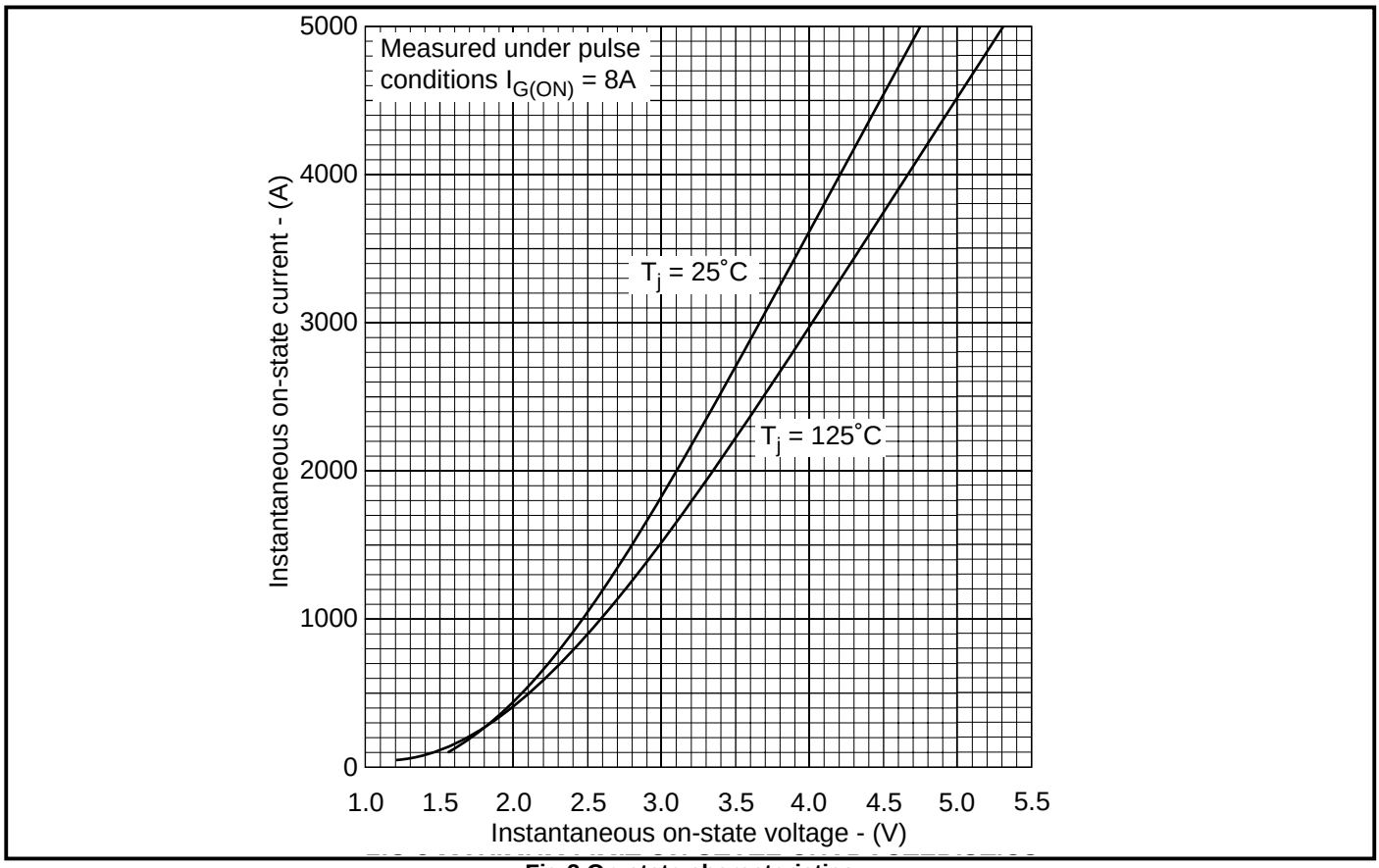


Fig.2 On-state characteristics

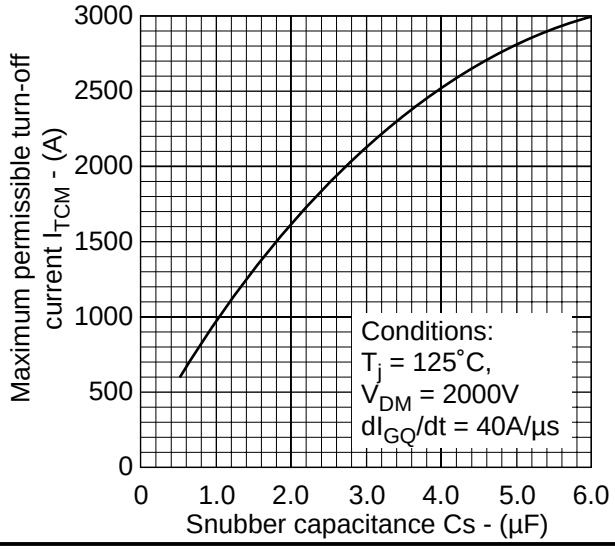


Fig.3 Maximum dependence of I_{TCM} on C_S

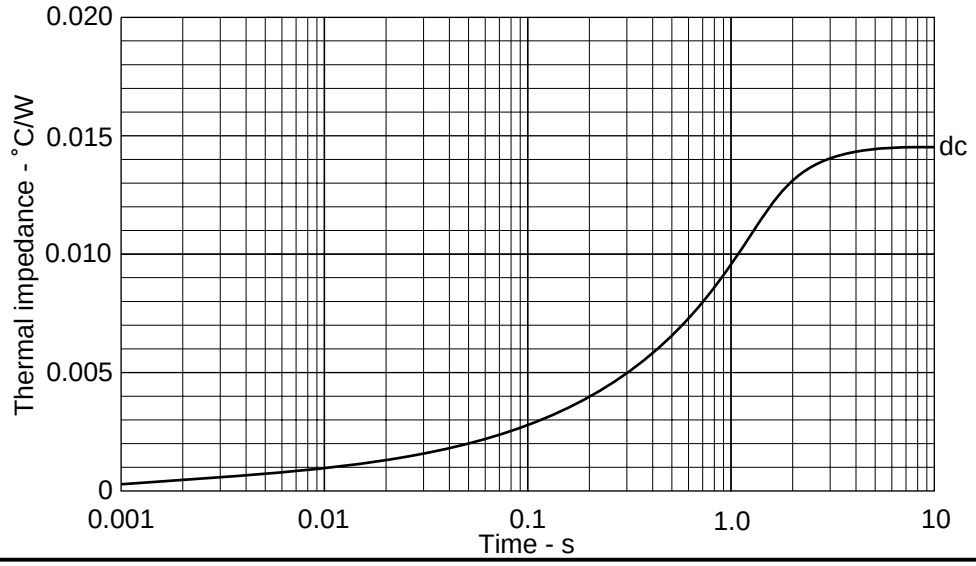


Fig.4 Maximum (limit) transient thermal impedance - double side cooled

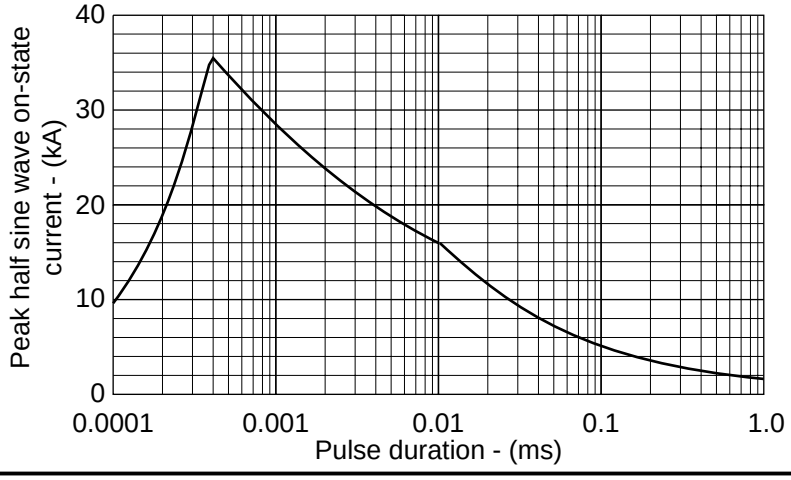


Fig.5 Surge (non-repetitive) on-state current vs time

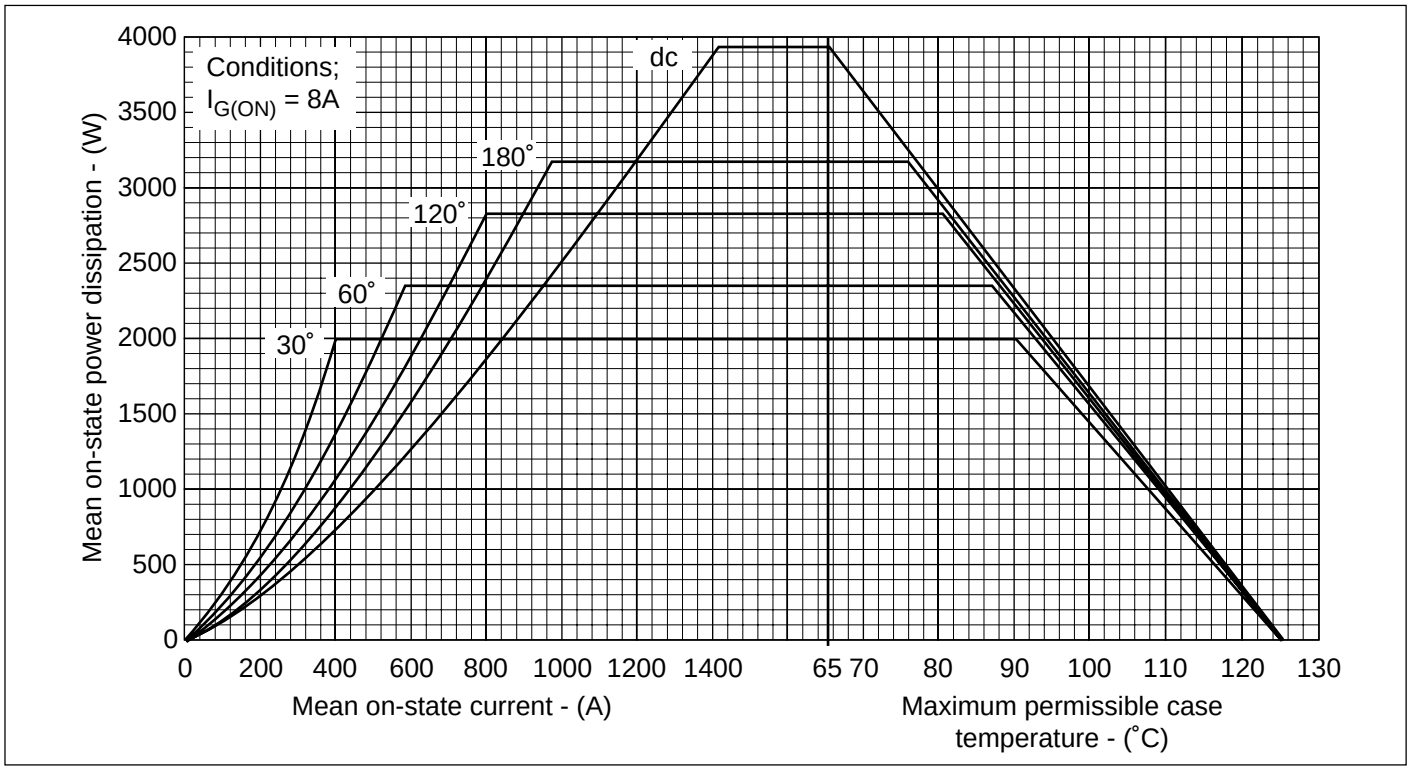


Fig.6 Steady state rectangluar wave conduction loss - double side cooled

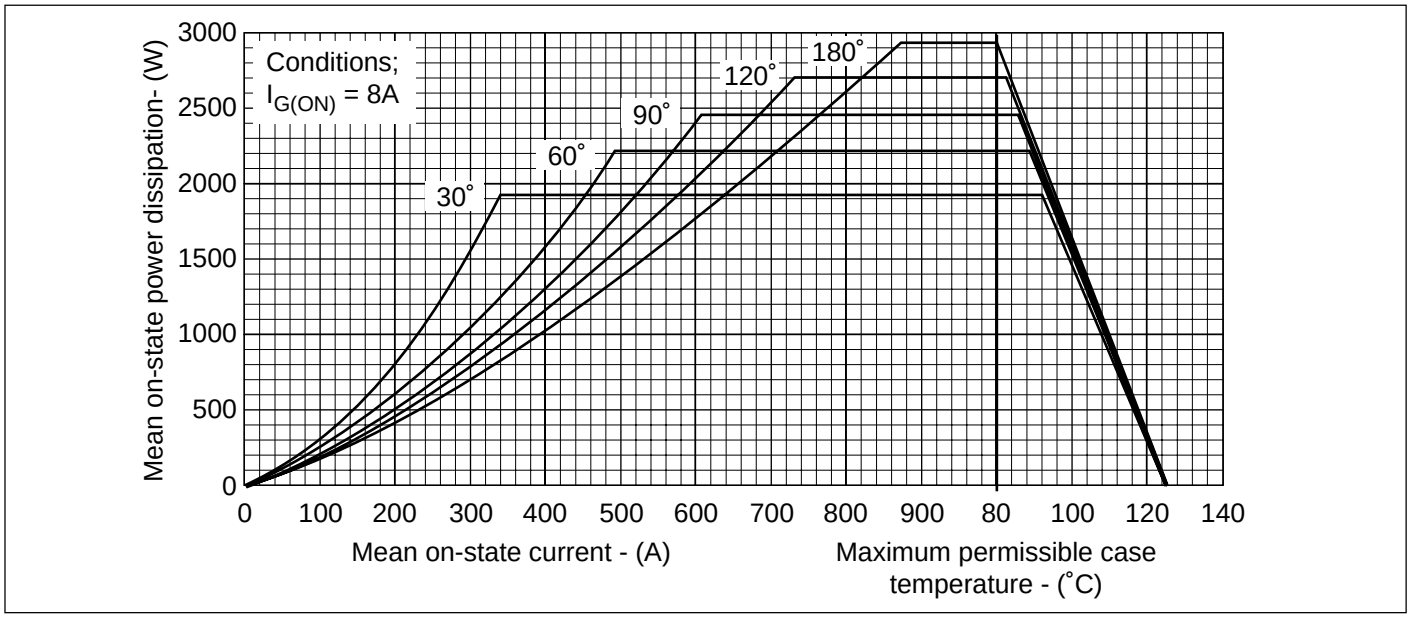


Fig.7 Steady state sinusoidal wave conduction loss - double side cooled

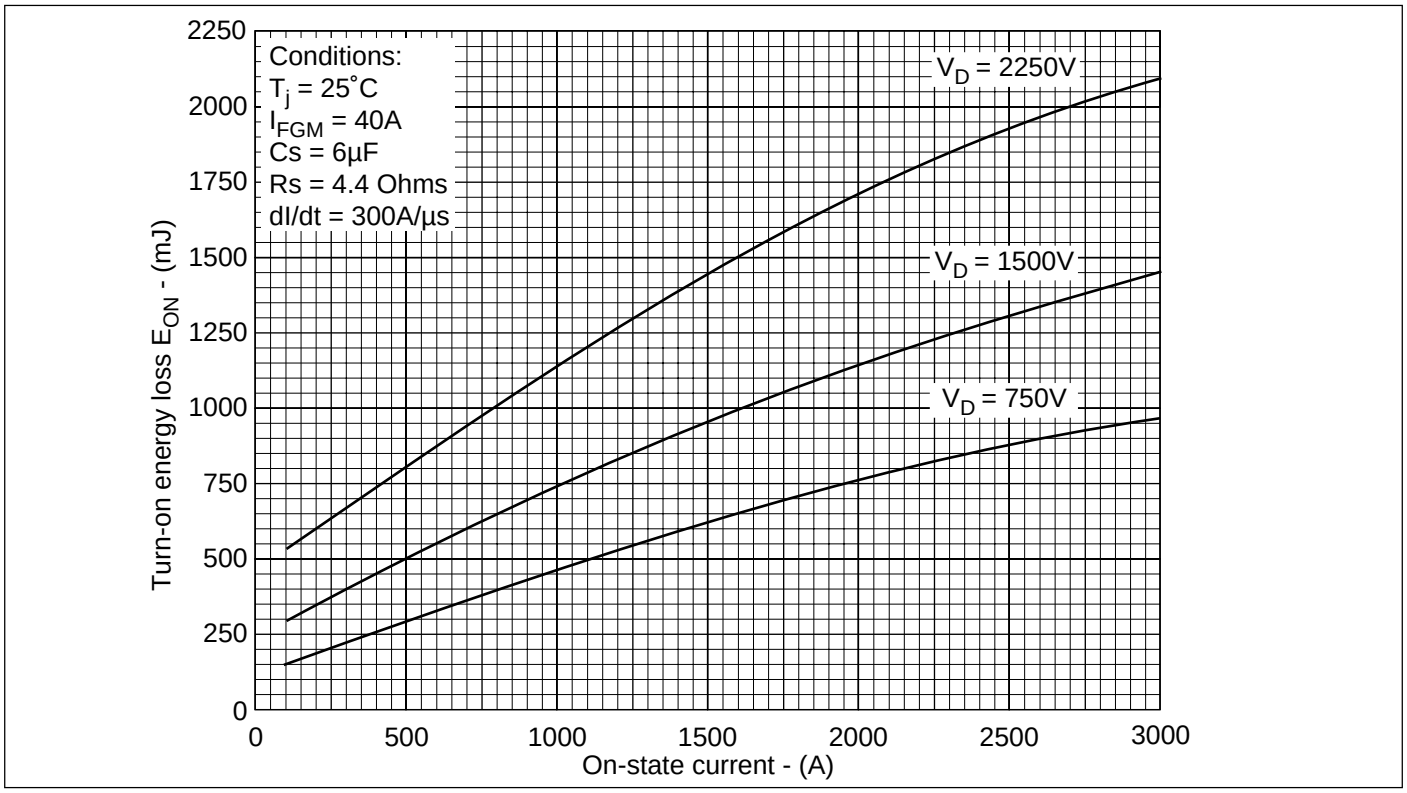


Fig.8 Turn-on energy vs on-state current

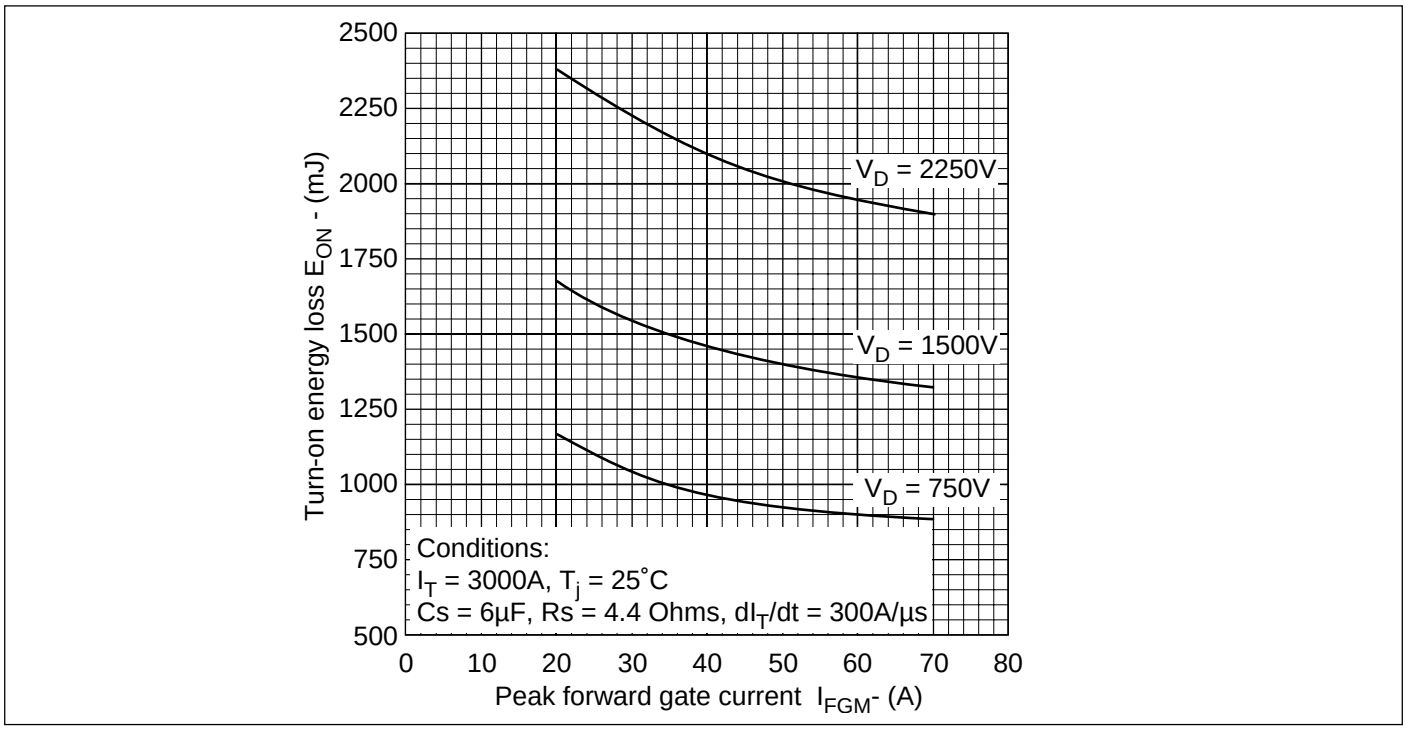


Fig.9 Turn-on energy vs peak forward gate current

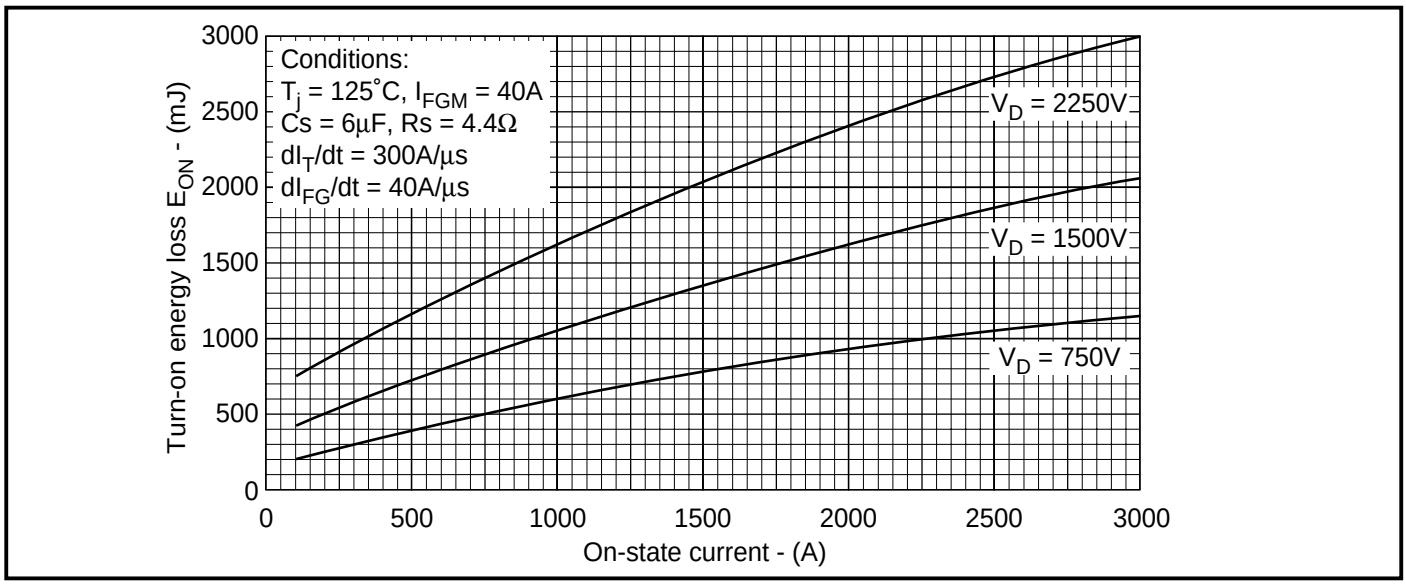


Fig.10 Turn-on energy vs on-state current

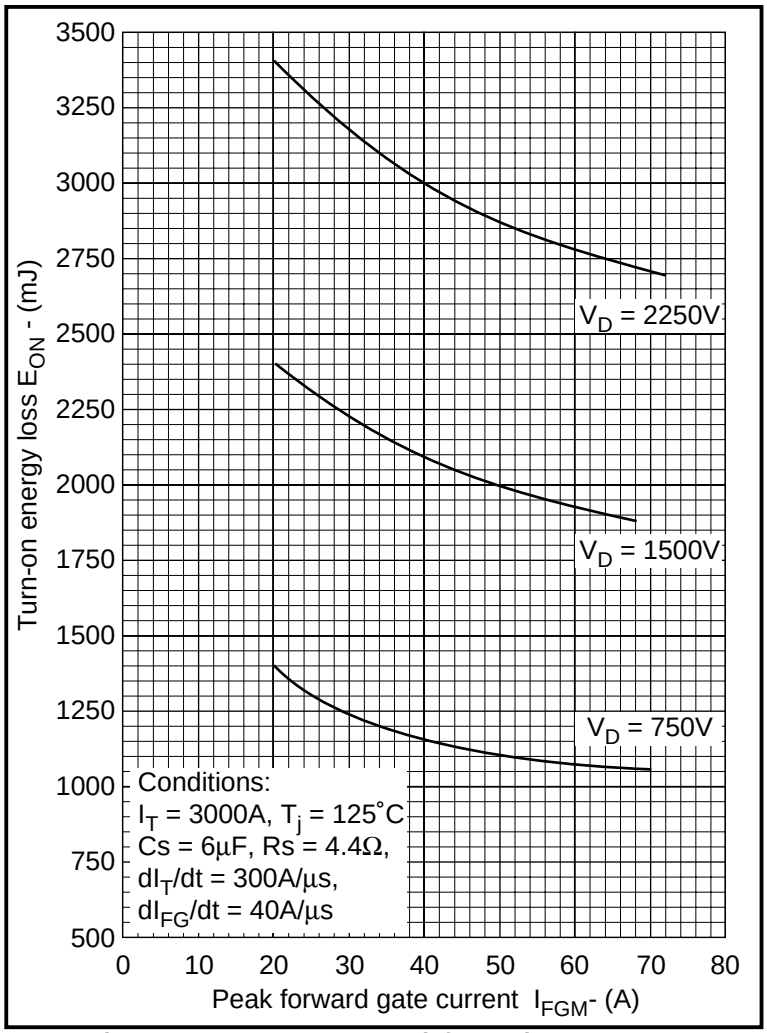


Fig.11 Turn-on energy vs peak forward gate current

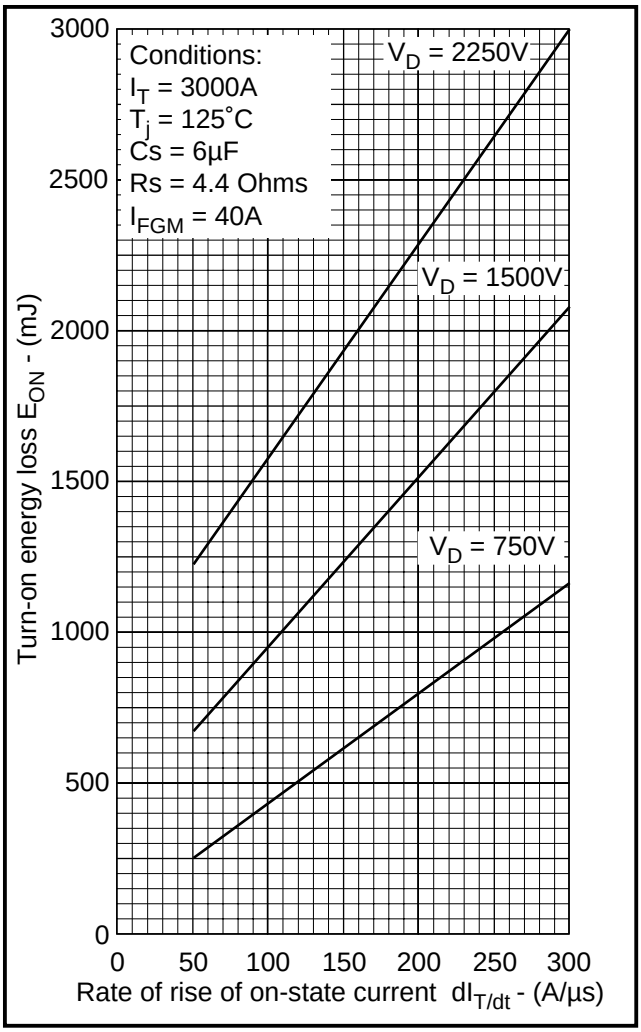


Fig.12 Turn-on energy vs rate of rise of on-state current

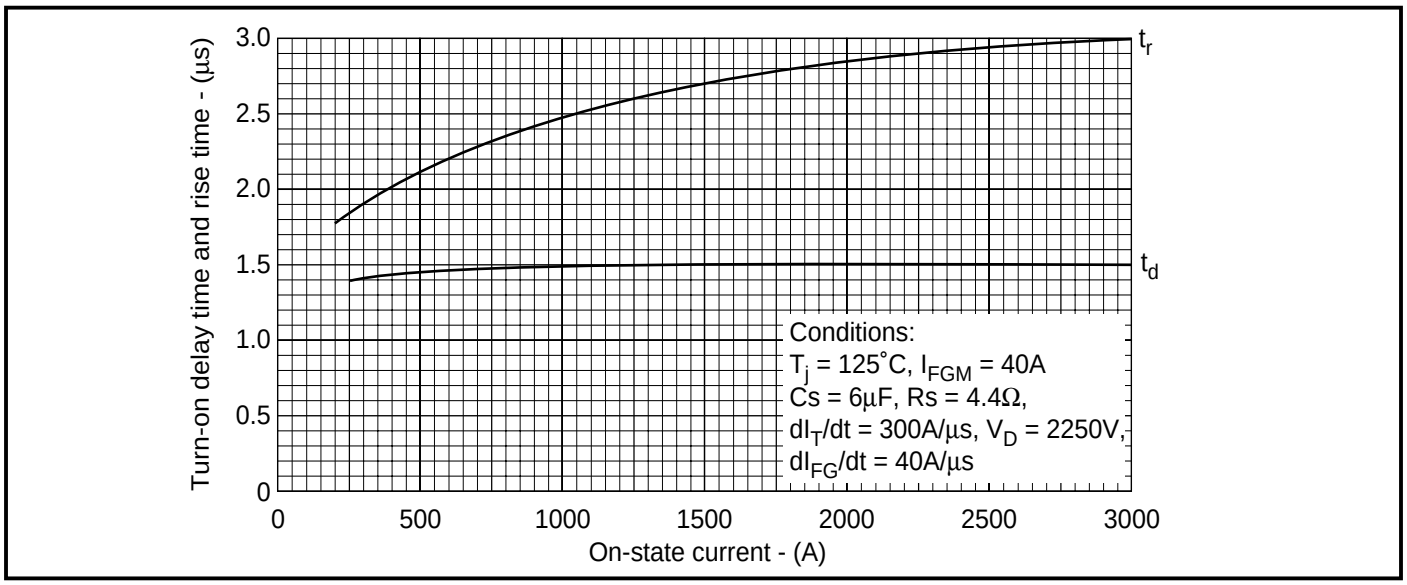


Fig.13 Delay time & rise time vs turn-on current

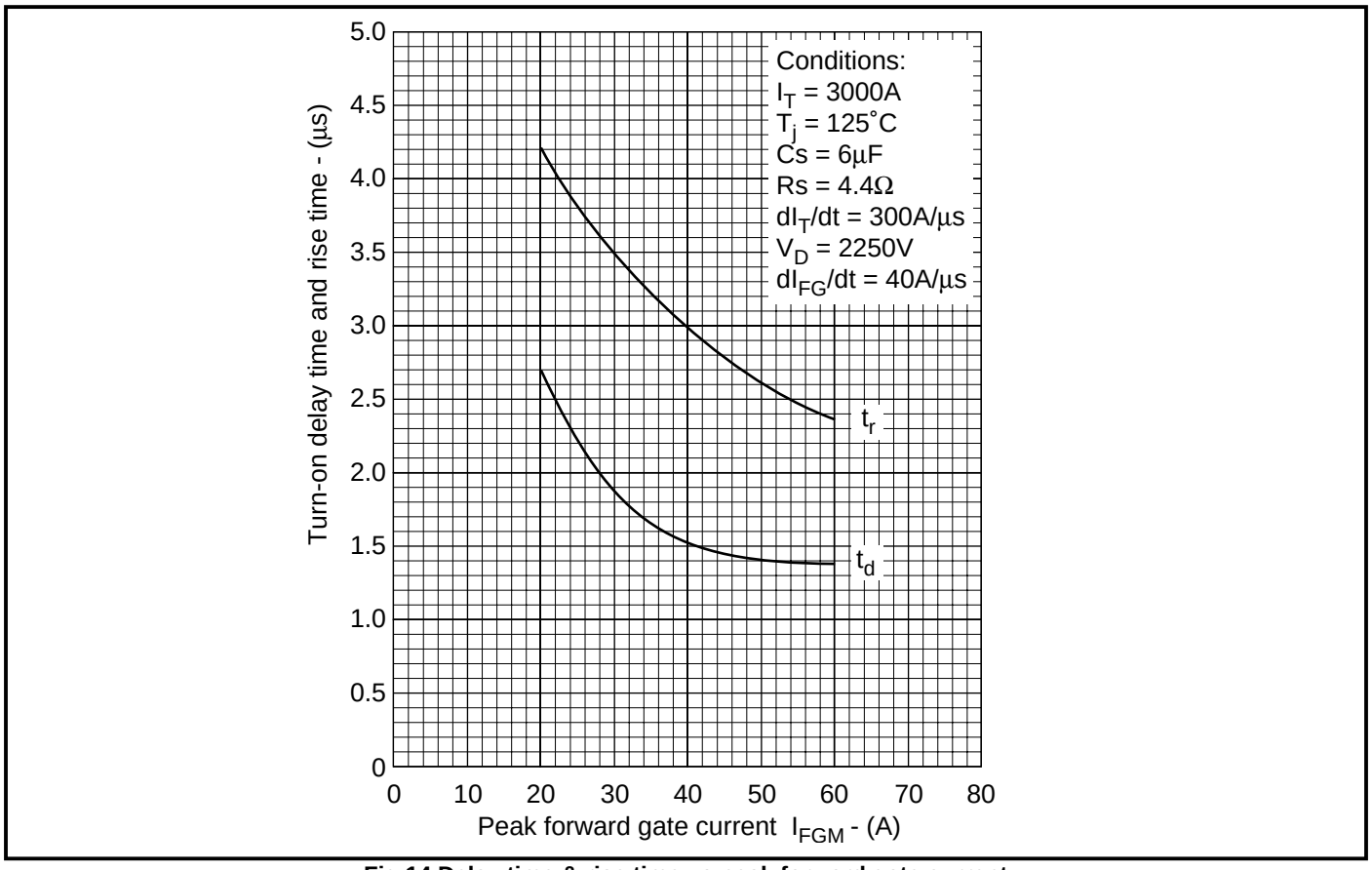


Fig.14 Delay time & rise time vs peak forward gate current

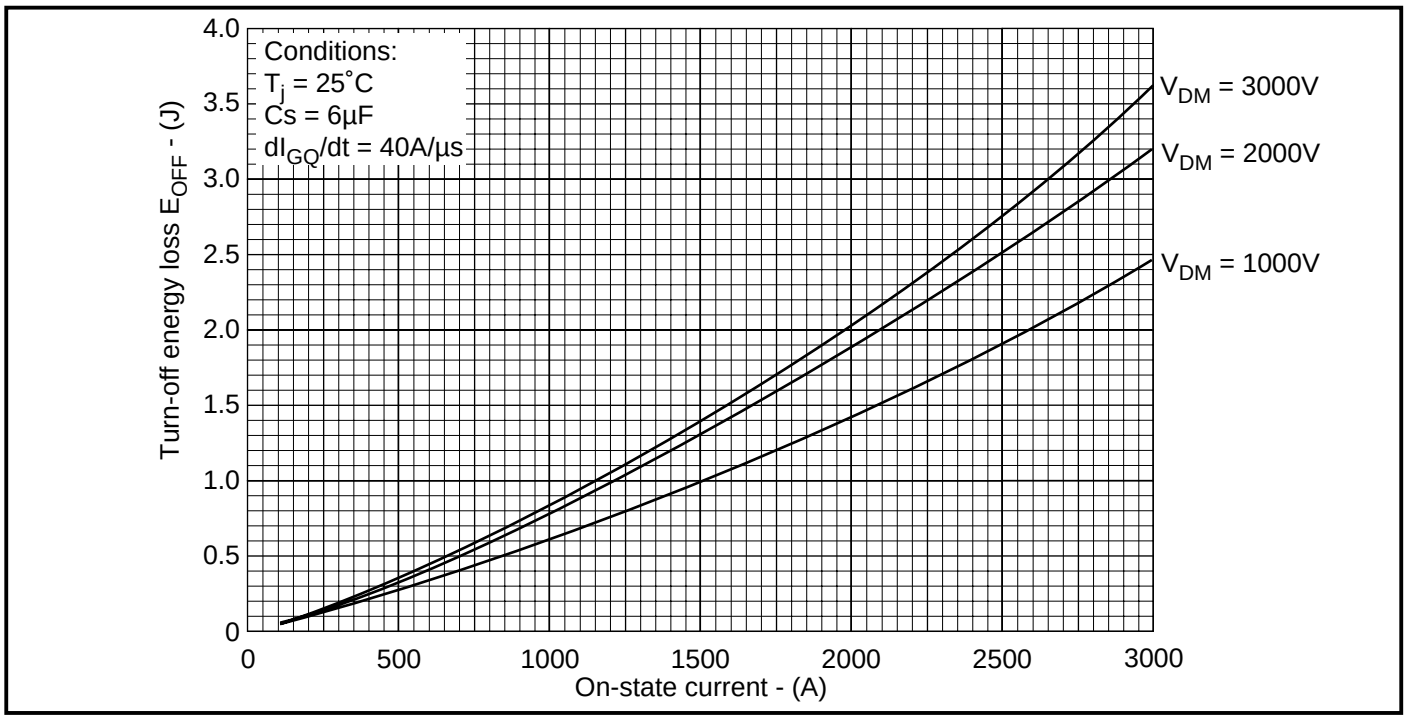


Fig.15 Turn-off energy vs on-state current

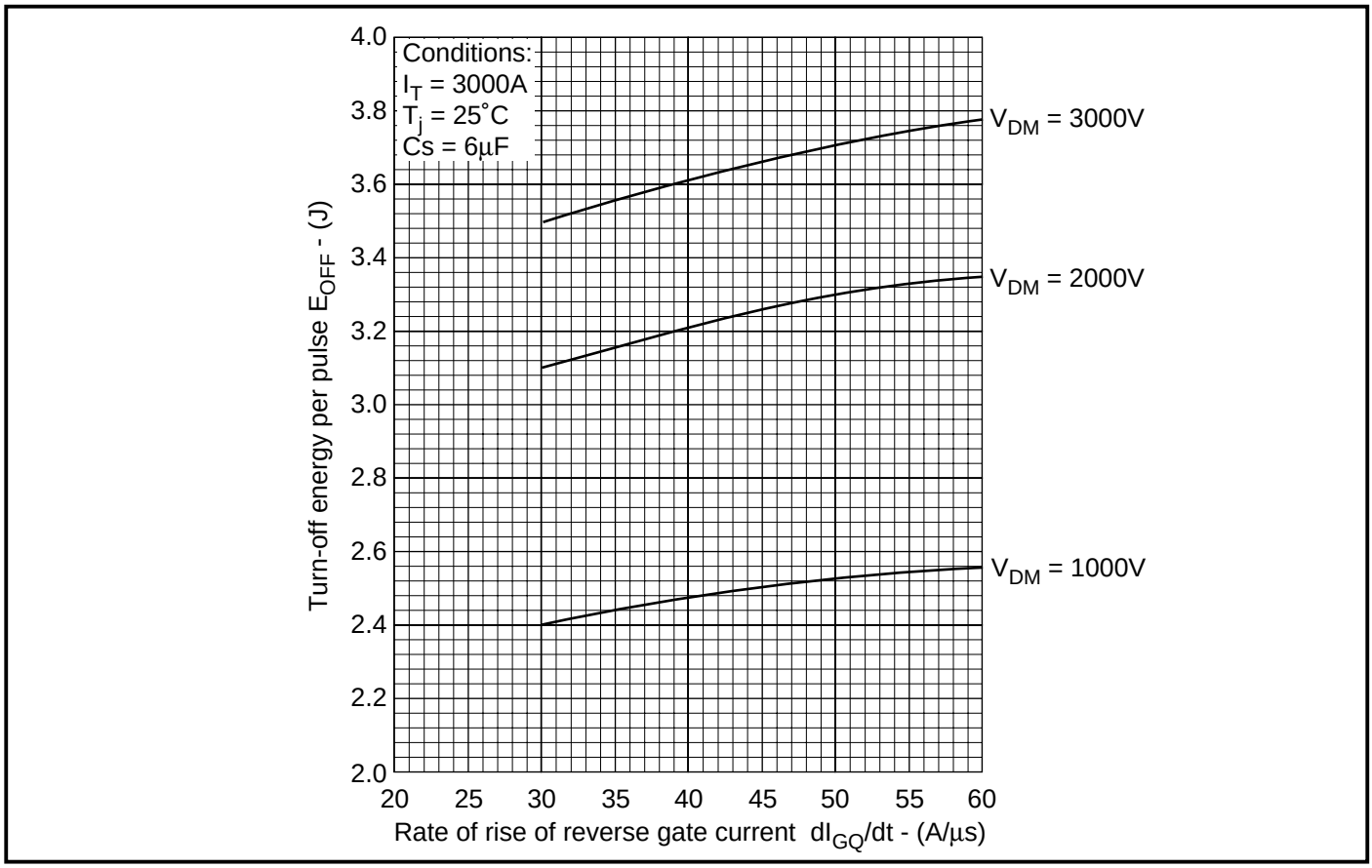


Fig.16 Turn-off energy vs rate of rise of reverse gate current

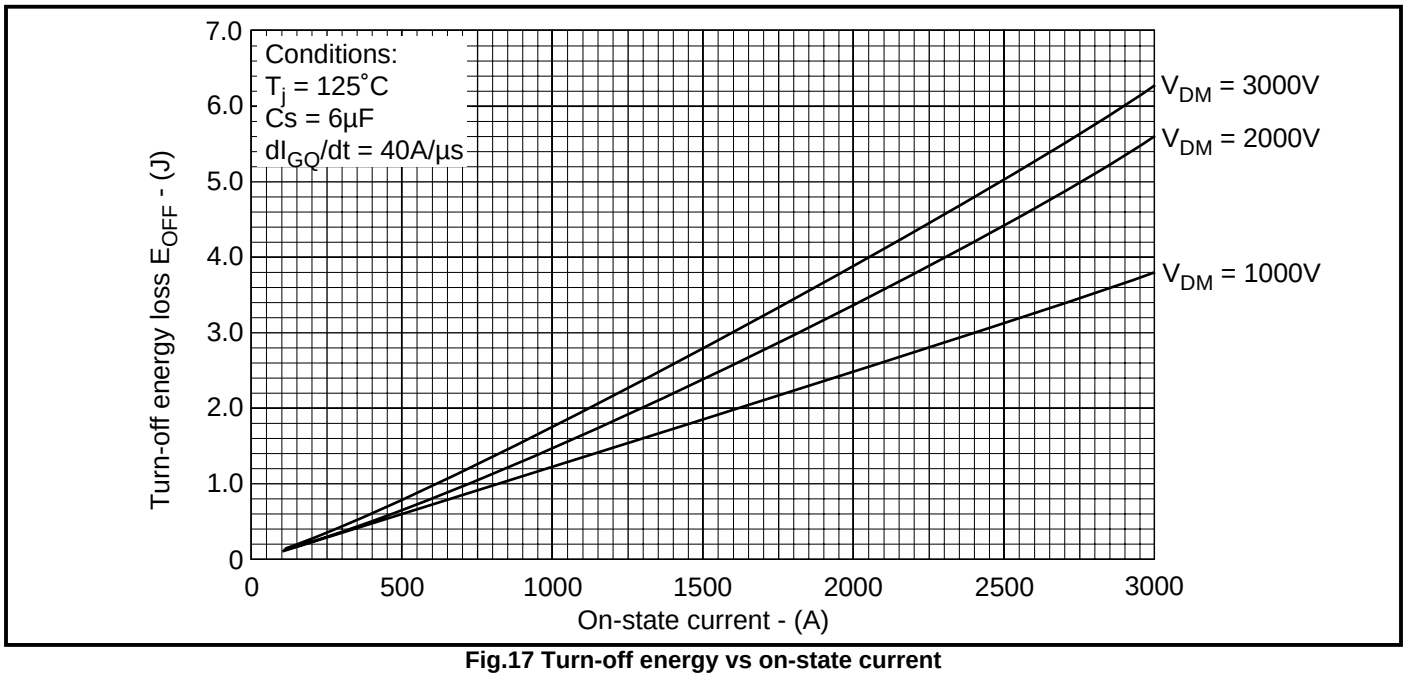


Fig.17 Turn-off energy vs on-state current

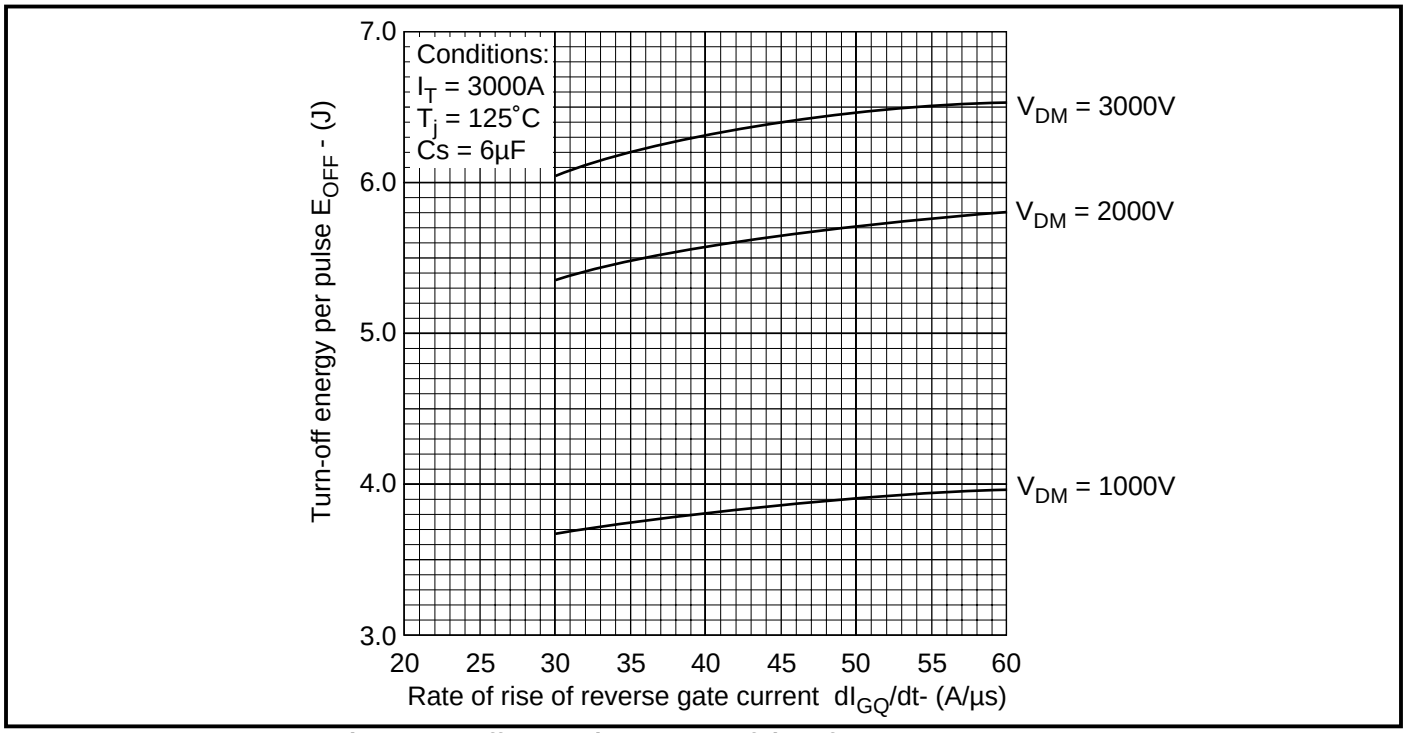


Fig.18 Turn-off energy loss vs rate of rise of reverse gate current

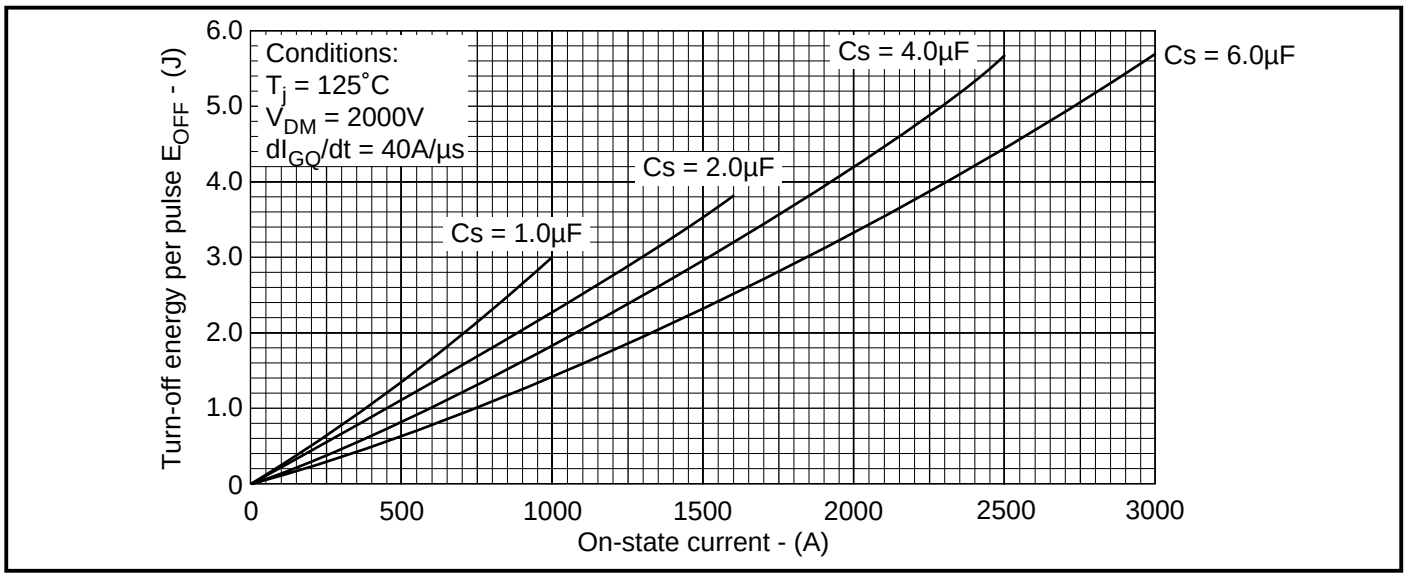


Fig.19 Turn-off energy vs on-state current

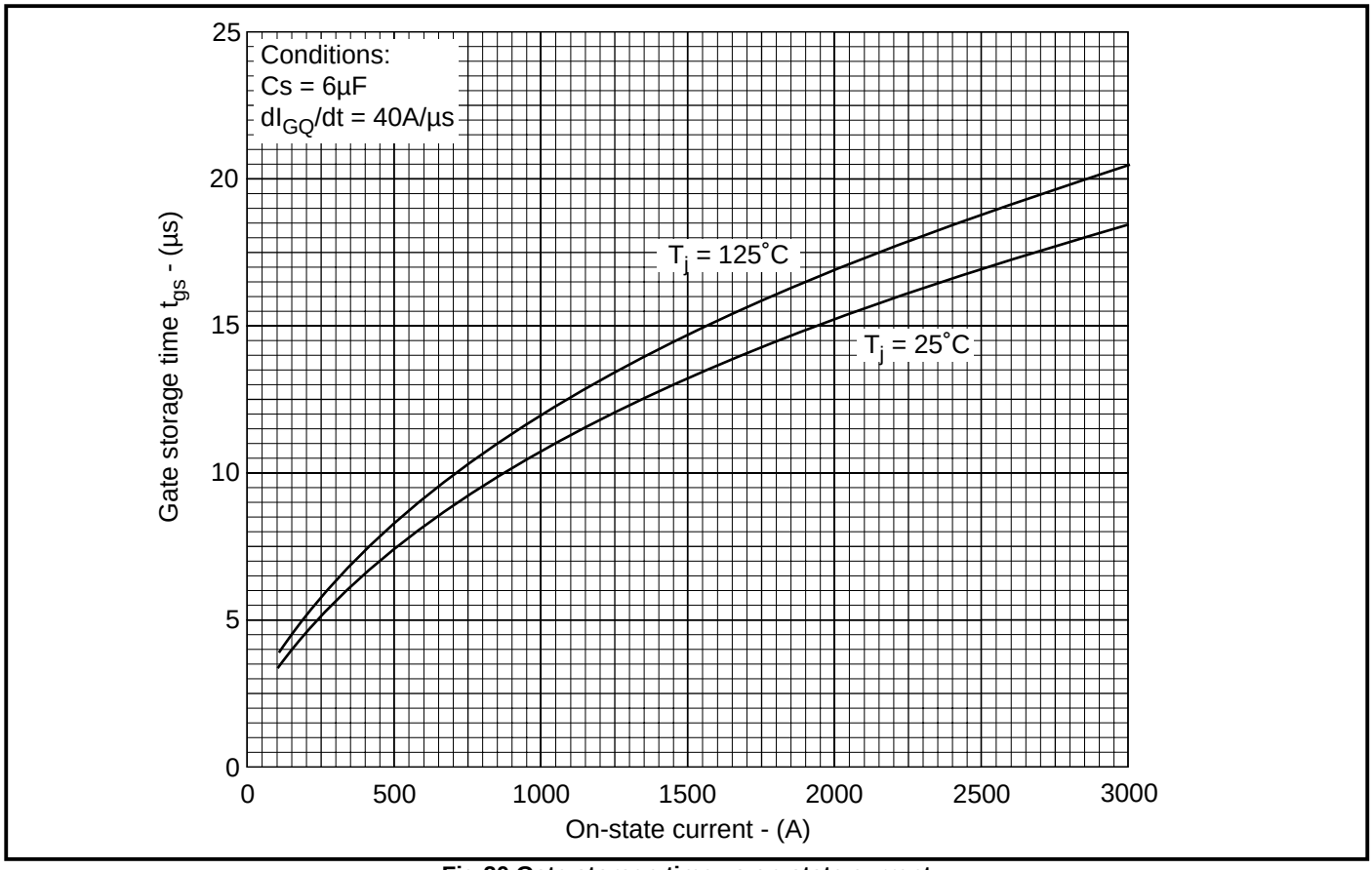


Fig.20 Gate storage time vs on-state current

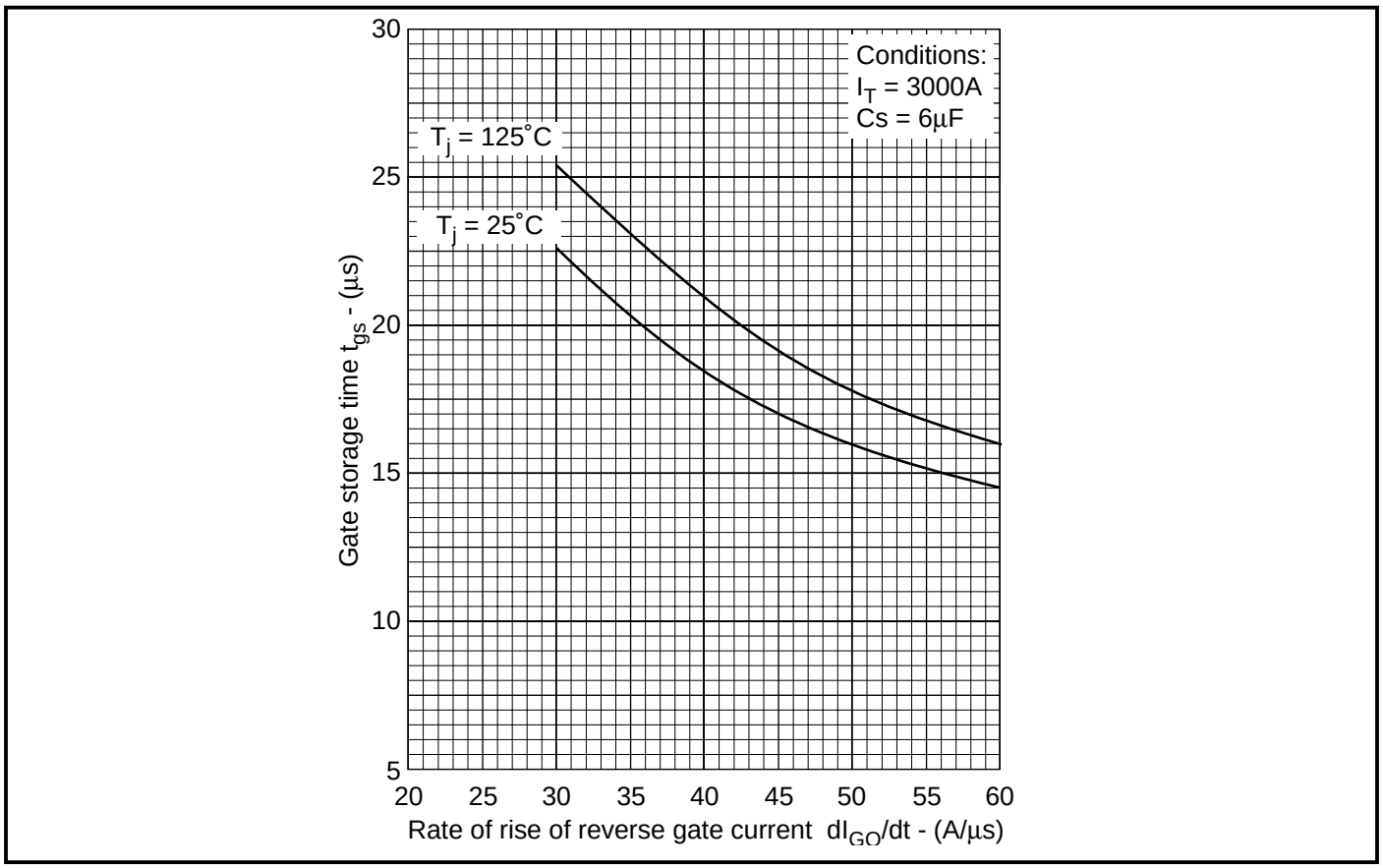


Fig.21 Gate storage time vs rate of rise of reverse gate current

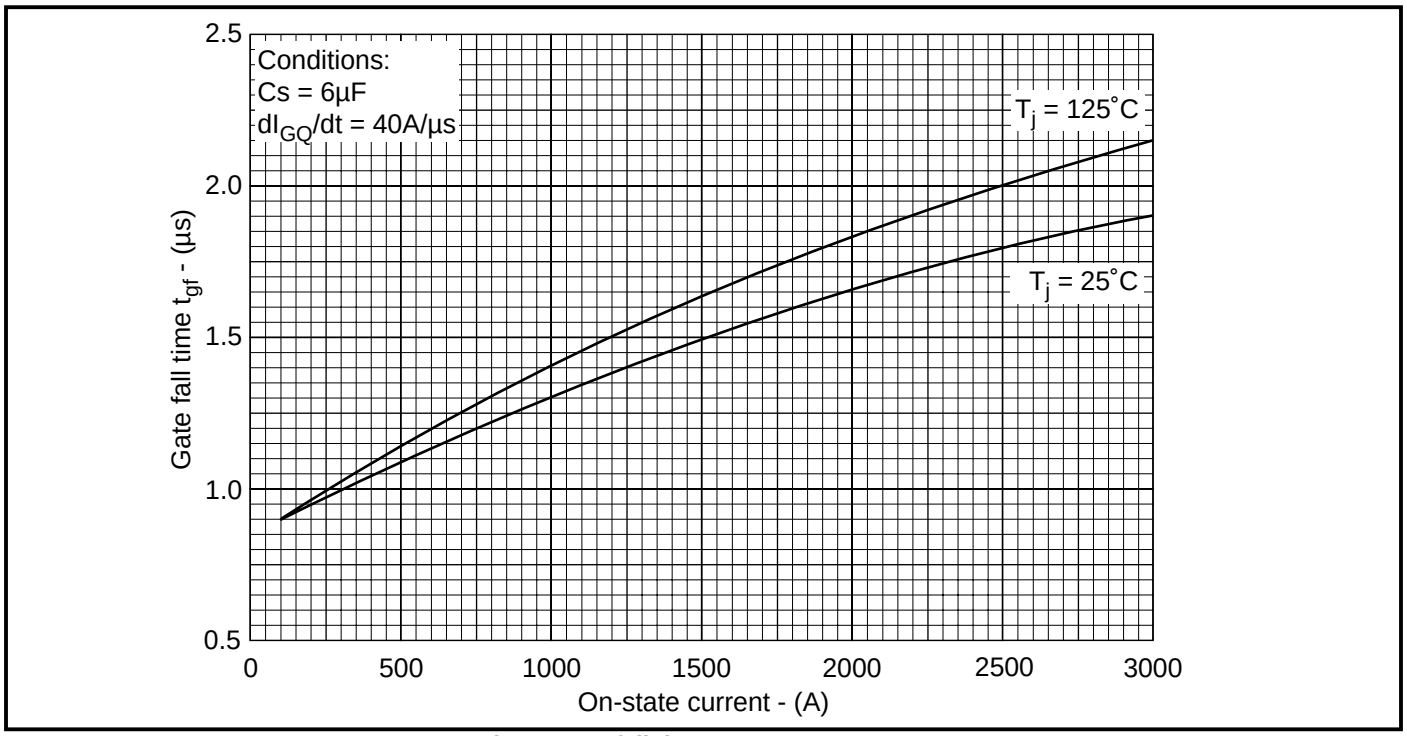


Fig.22 Gate fall time vs on-state current

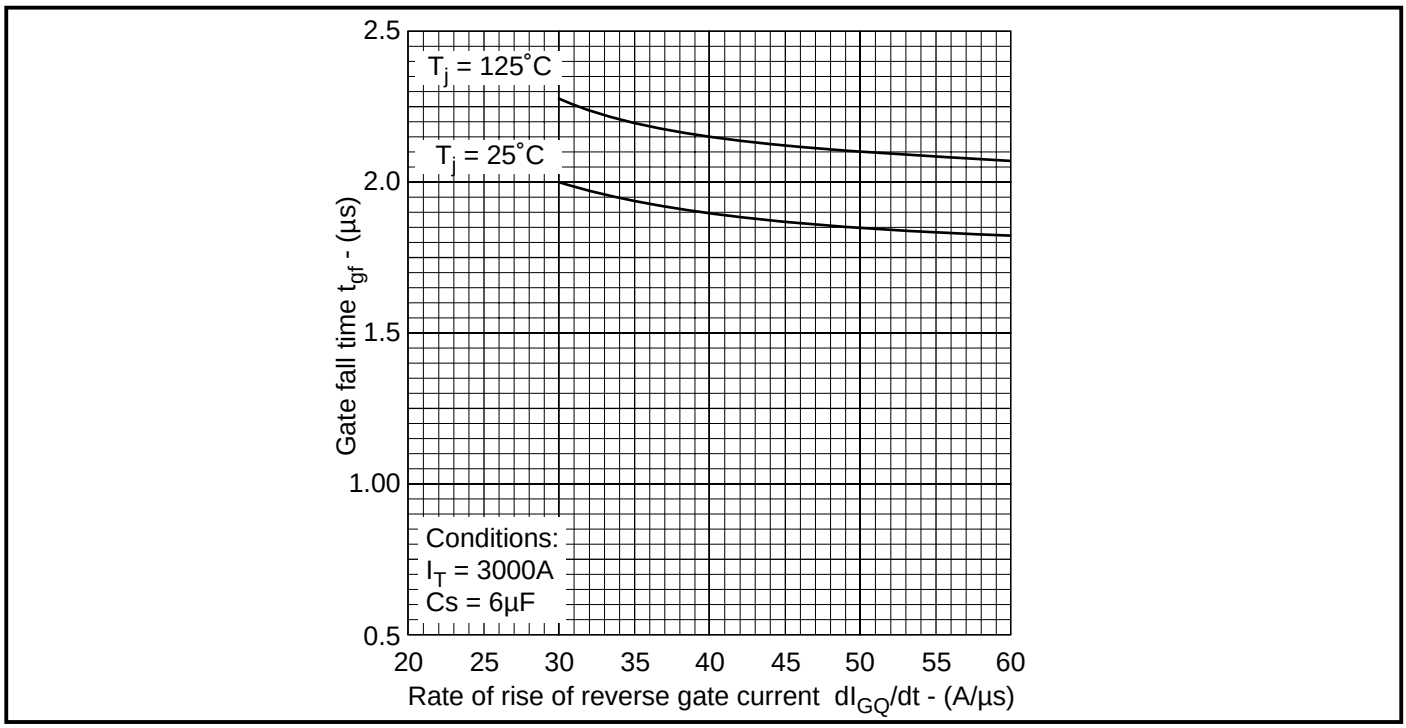


Fig.23 Gate fall time vs rate of rise of reverse gate current

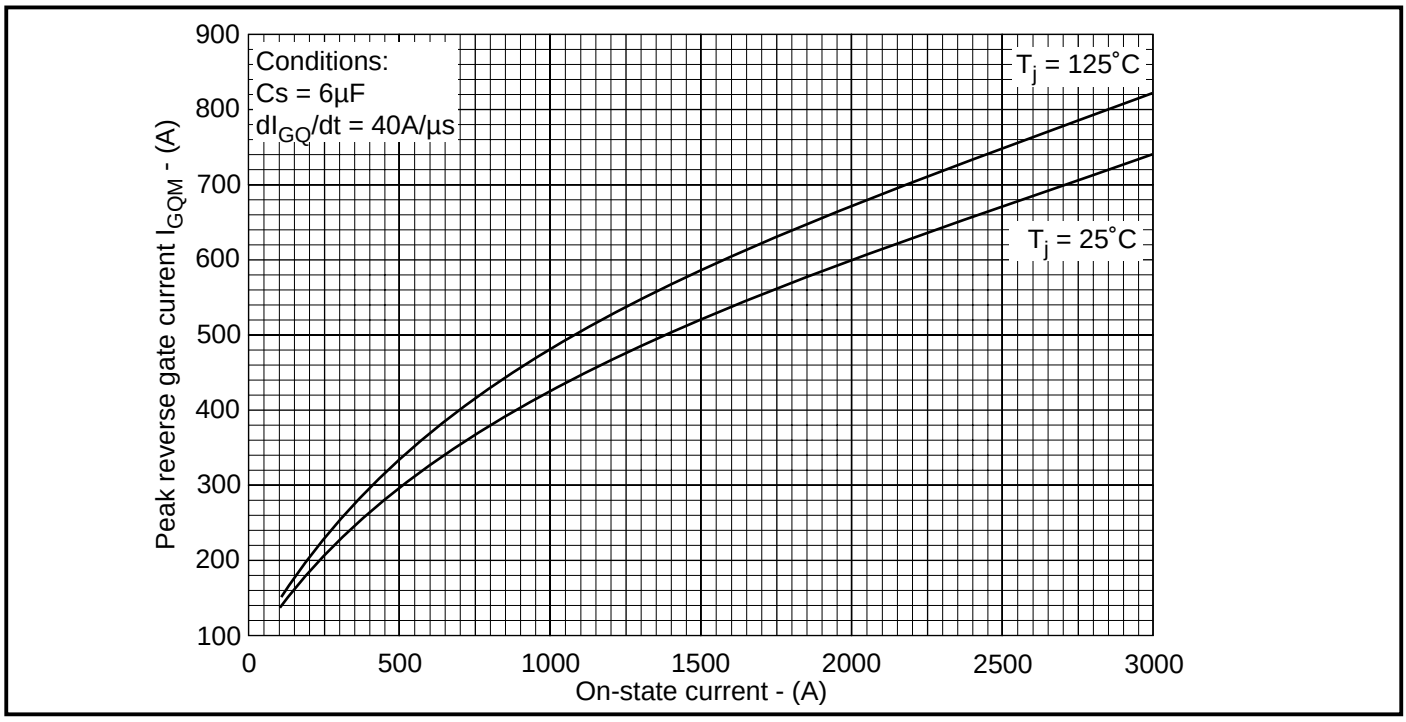


Fig.24 Peak reverse gate current vs turn-off current

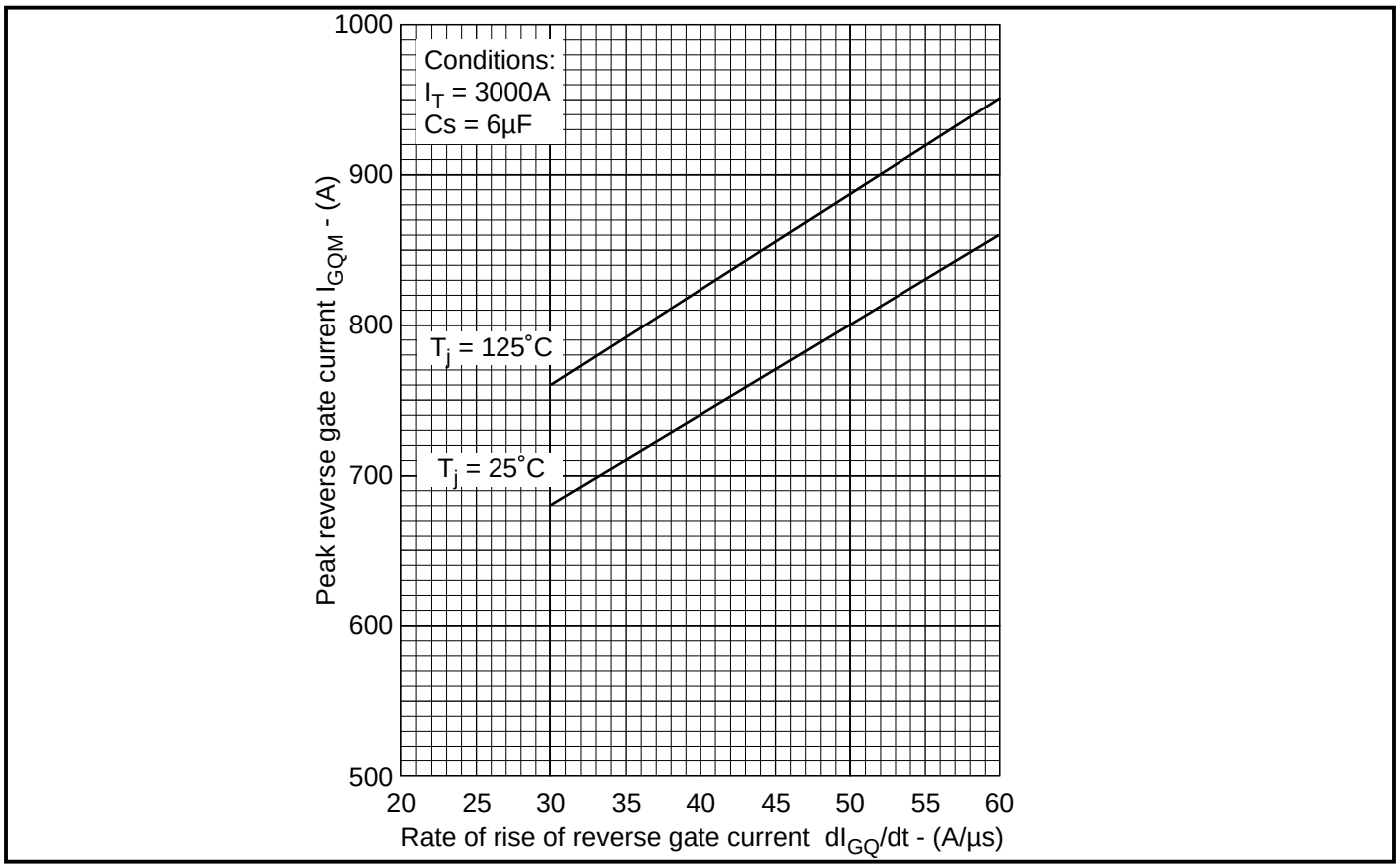


Fig.25 Peak reverse gate current vs rate of rise of reversegate current

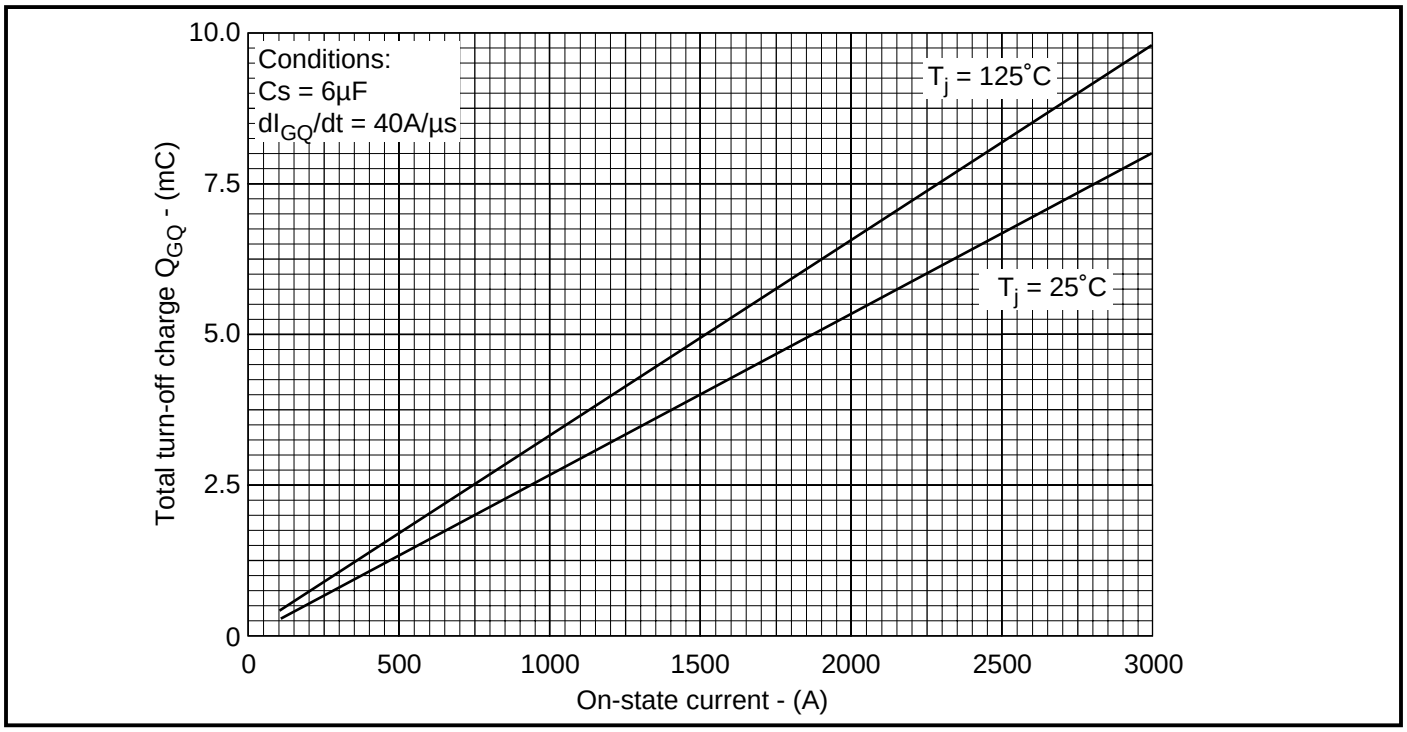


Fig.26 Turn-off gate charge vs on-state current

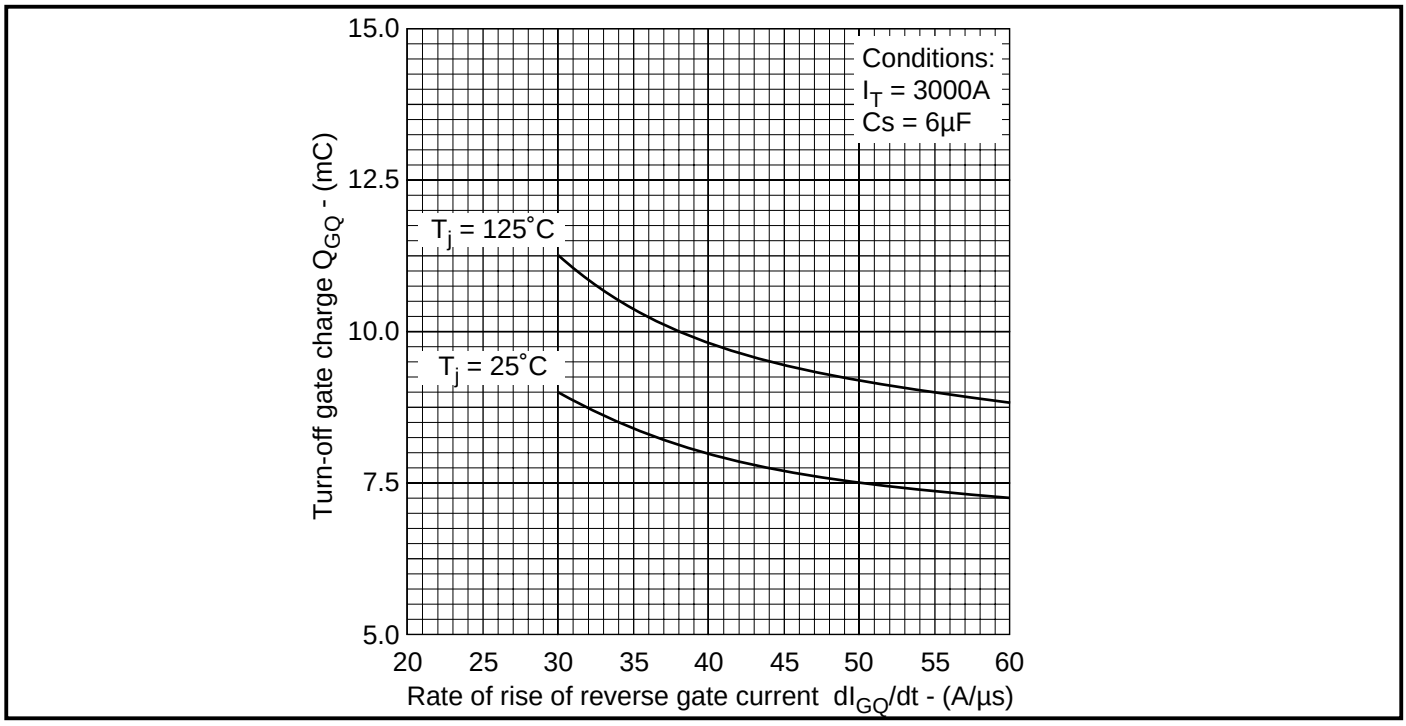


Fig.27 Turn-off gate charge vs rate of rise of reverse gate current

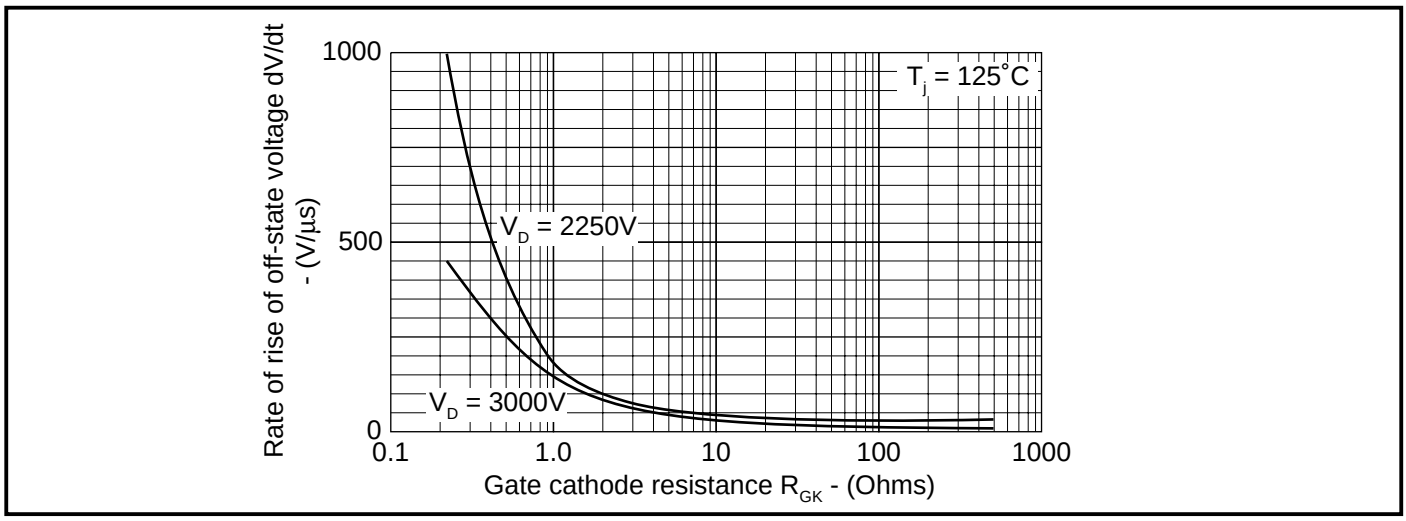
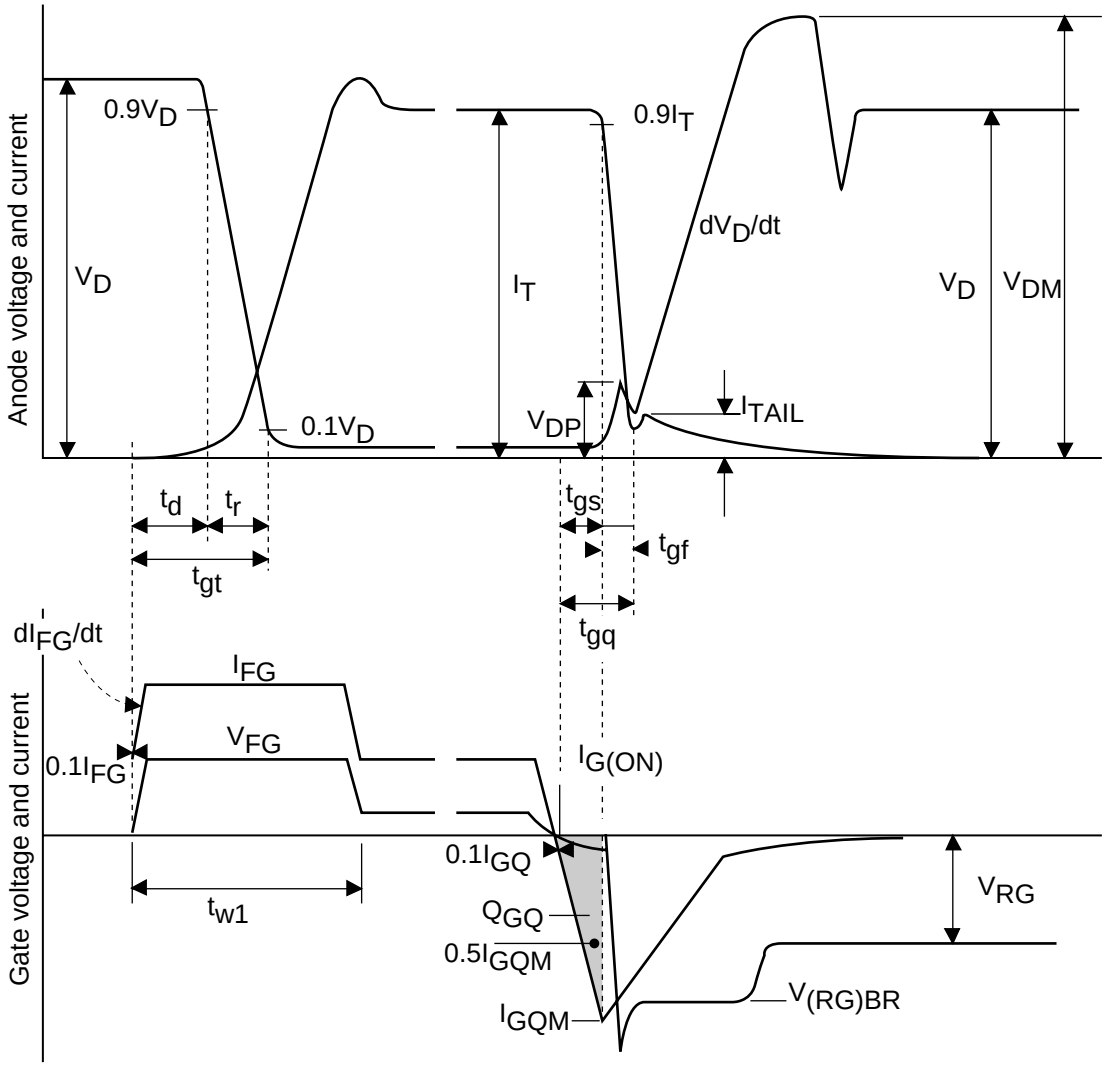


Fig.28 Rate of rise of off-state voltage vs gate cathode resistance



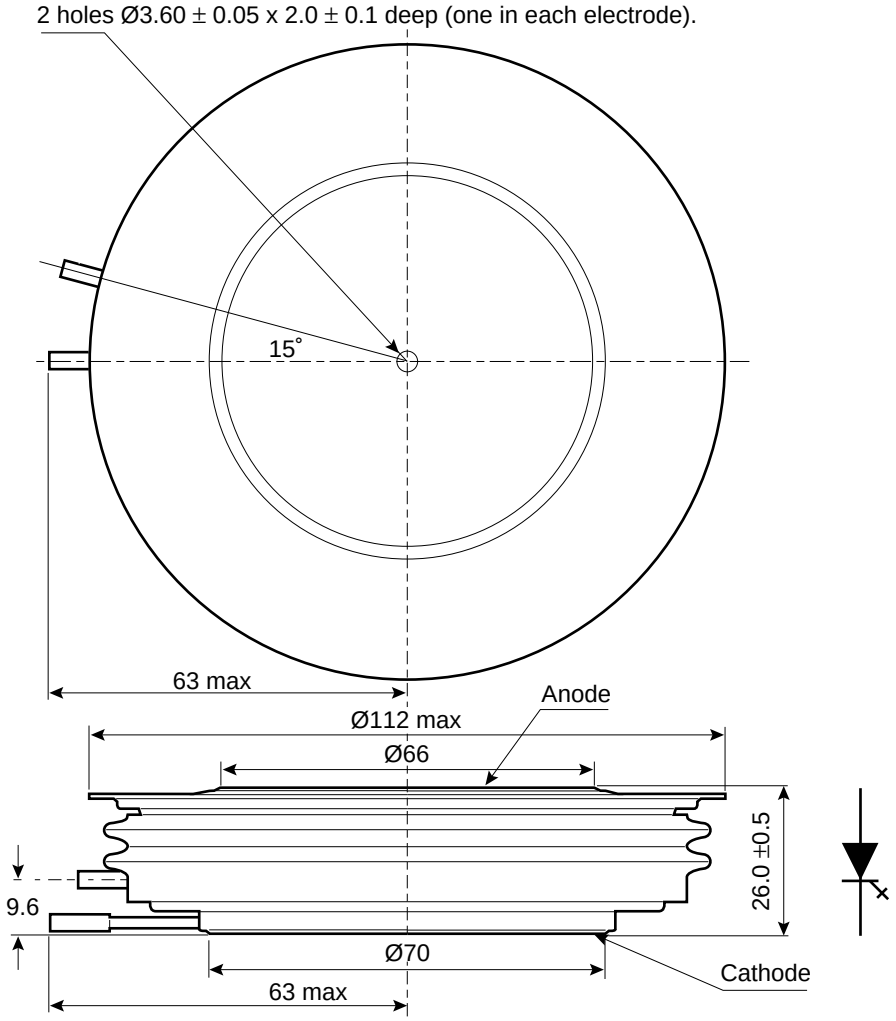
Recommended gate condition:
I_{TCM} = 3000A
I_{FG} = 40A
$I_{G(ON)}$ = 8A d.c.
$t_{w1(min)}$ = 10µs
I_{GQM} = 830A
di_{GQ}/dt = 40A/µs
Q_{GQ} = 10000µC
$V_{RG(min)}$ = 2V
$V_{RG(max)}$ = 16V

These are recommended Mitel Semiconductor conditions. Other conditions are permitted according to users gate drive specifications.

Fig.29 General switching waveforms

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal weight: 1200g
Clamping force: 35kN ±10%
Lead length: 505mm

Package outine type code: X

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

DYNEX SEMICONDUCTOR

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Datasheet Annotations:

Dynex Semiconductor annotate datasheets in the top right hard corner of the front page, to indicate product status. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.